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### **General Description**

The MAX1718 step-down controller is intended for core CPU DC-DC converters in notebook computers. It features a dynamically adjustable output, ultra-fast transient response, high DC accuracy, and high efficiency needed for leading-edge CPU core power supplies. Maxim's proprietary Quick-PWM™ quick-response, constant-ontime PWM control scheme handles wide input/output voltage ratios with ease and provides 100ns "instant-on" response to load transients while maintaining a relatively constant switching frequency.

The output voltage can be dynamically adjusted through the 5-bit digital-to-analog converter (DAC) over a 0.6V to 1.75V range. The MAX1718 has an internal multiplexer that accepts three unique 5-bit VID DAC codes corresponding to Performance, Battery, and Suspend modes. Precision slew-rate control provides "just-in-time" arrival at the new DAC setting, minimizing surge currents to and from the battery.

The internal DAC of the MAX1718B is synchronized to the slew-rate clock for improved operation under aggressive power management of newer chipsets and operating systems that can make incomplete mode transitions.

A pair of complementary offset control inputs allows easy compensation for IR drops in PC board traces or creation of a voltage-positioned power supply. Voltagepositioning modifies the load-transient response to reduce output capacitor requirements and total system power dissipation.

Single-stage buck conversion allows these devices to directly step down high-voltage batteries for the highest possible efficiency. Alternatively, two-stage conversion (stepping down the 5V system supply instead of the battery) at a higher switching frequency allows the minimum possible physical size.

The MAX1718 is available in a 28-pin QSOP package.

### **Applications**

IMVP-II™ Notebook Computers 2-Cell to 4-Cell Li+ Battery to CPU Core Supply Converters

5V to CPU Core Supply Converters

Pin Configuration appears at end of data sheet.

Quick-PWM is a trademark of Maxim Integrated Products, Inc. IMVP-II is a trademark of Intel Corp.

#### Features

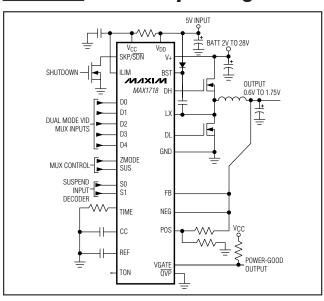
- **♦ Quick-PWM Architecture**
- **♦** ±1% Vout Accuracy Over Line and Load
- ♦ 5-Bit On-Board DAC with Input Muxes
- ♦ Precision-Adjustable Vout Slew Control
- ♦ 0.6V to 1.75V Output Adjust Range
- **♦ Precision Offset Control**
- **♦** Supports Voltage-Positioned Applications
- ♦ 2V to 28V Battery Input Range
- ♦ Requires a Separate 5V Bias Supply
- ♦ 200/300/550/1000kHz Switching Frequency
- ♦ Over/Undervoltage Protection
- ♦ Drives Large Synchronous-Rectifier FETs
- ♦ 700µA (typ) I<sub>CC</sub> Supply Current
- ♦ 2µA (typ) Shutdown Supply Current
- ♦ 2V ±1% Reference Output
- **♦ VGATE Blanking During Transition**
- ♦ Small 28-Pin QSOP Package

### **Ordering Information**

PART	TEMP RANGE	PIN-PACKAGE
MAX1718EEI	-40°C to +85°C	28 QSOP
MAX1718BEEI+	-40°C to +85°C	28 QSOP
MAX1718BEEI	-40°C to +85°C	28 QSOP
MAX1718BEEIB+	-40°C to +85°C	28 QSOP

<sup>+</sup>Denotes lead-free package.

### **Minimal Operating Circuit**



Maxim Integrated Products 1

### **ABSOLUTE MAXIMUM RATINGS**

V+ to GND0.3V to +	-30V
V <sub>CC</sub> , V <sub>DD</sub> to GND0.3V to	+6V
D0-D4, ZMODE, VGATE, OVP, SUS, to GND0.3V to	+6V
SKP/SDN to GND0.3V to 4	-16V
ILIM, CC, REF, POS, NEG, S1, S0,	
TON, TIME to GND0.3V to (V <sub>CC</sub> + 0	).3V)
DL to GND0.3V to (V <sub>DD</sub> + 0	).3V)
BST to GND0.3V to 4	-36V
DH to LX0.3V to (BST + 0	).3V)

LX to BST	6V to +0.3V
REF Short Circuit to GND	Continuous
Continuous Power Dissipation	
28-Pin QSOP (derate 10.8mW/°C above	ve +70°C)860mW
Operating Temperature Range	40°C to +85°C
Junction Temperature	+150°C
Storage Temperature	65°C to +150°C
Lead Temperature (soldering, 10s)	+300°C

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

### **ELECTRICAL CHARACTERISTICS**

(Circuit of Figure 1, V+ = 15V, V<sub>CC</sub> = V<sub>DD</sub> = SKP/SDN = 5V, V<sub>OUT</sub> = 1.25V, T<sub>A</sub> = 0°C to +85°C, unless otherwise noted.)

PARAMETER	CONDITIONS		MIN	TYP	MAX	UNITS	
PWM CONTROLLER	ı						
land Walterna Danasa	Battery voltage, V+		2		28	.,,	
Input Voltage Range	V <sub>CC</sub> , V <sub>DD</sub>			4.5		5.5	V
DC Output Voltage Accuracy	V+ = 4.5V to 28V, includes load	DAC	codes from 0.9V to 1.75V	-1		+1	%
Do output voltage / toodracy	regulation error	DAC	codes from 0.6V to 0.875V	-1.5		+1.5	%
Line Regulation Error	$V_{CC} = 4.5V \text{ to } 5.5V, V$	/ <sub>BATT</sub> =	4.5V to 28V		5		mV
Input Bias Current	FB, POS, NEG			-0.2		+0.2	μΑ
POS, NEG Common-Mode Range				0.4		2.5	V
POS, NEG Differential Range	POS - NEG			-80		+80	mV
POS, NEG Offset Gain	$\Delta V_{FB}$ / (POS - NEG);	POS - N	NEG = 50mV	0.81	0.86	0.91	V/V
	150kHz nominal, $R_{TIME} = 120kΩ$		-8		+8		
TIME Frequency Accuracy	380kHz nominal, $R_{TIME} = 47k\Omega$		-12		+12	%	
	38kHz nominal, R <sub>TIME</sub> = $470$ k $\Omega$		-12		+12	1	
	V+ = 5V, FB = 1.2V, TON = GND (1000kHz)		230	260	290		
On Time (NI-to 1)	V+ = 12V, FB = 1.2V		165	190	215	1	
On-Time (Note 1)			TON = open (300kHz)	320	355	390	- ns
			TON = V <sub>CC</sub> (200kHz)	465	515	565	
M: : Off T: (N + 4)	TON = V <sub>CC</sub> , open, or REF (200kHz, 300kHz, or 550kHz)			400	500		
Minimum Off-Time (Note 1)	TON = GND (1000kHz)			300	375	ns	
BIAS AND REFERENCE							
Quiescent Supply Current (V <sub>CC</sub> )	Measured at V <sub>CC</sub> , FE	3 forced	above the regulation point		700	1200	μΑ
Quiescent Supply Current (V <sub>DD</sub> )	Measured at V <sub>DD</sub> , FE	3 forced	above the regulation point		<1	5	μΑ
Quiescent Battery Supply Current (V+)				25	40	μА	
Shutdown Supply Current (VCC)	SKP/SDN = GND			2	5	μΑ	
Shutdown Supply Current (V <sub>DD</sub> )	SKP/SDN = GND			<1	5	μΑ	
Shutdown Battery Supply Current (V+)	SKP/SDN = GND, V <sub>CC</sub> = V <sub>DD</sub> = 0V or 5V				<1	5	μA
Reference Voltage	$V_{CC} = 4.5V \text{ to } 5.5V, r$	no REF I	load	1.98	2	2.02	V

### **ELECTRICAL CHARACTERISTICS (continued)**

(Circuit of Figure 1, V + = 15V,  $V_{CC} = V_{DD} = SKP/\overline{SDN} = 5V$ ,  $V_{OUT} = 1.25V$ ,  $T_A = 0^{\circ}C$  to +85°C, unless otherwise noted.)

PARAMETER	CONDITIONS		MIN	TYP	MAX	UNITS
Reference Load Regulation	I <sub>REF</sub> = 0μA to 50μA				0.01	V
REF Sink Current	REF in regulation		10			μΑ
FAULT PROTECTION						
Overvoltage Trip Threshold	Measured at FB		1.95	2.00	2.05	V
Overvoltage Fault Propagation Delay	FB forced 2% above trip to	hreshold		10		μs
Output Undervoltage Fault Protection Threshold	With respect to unloaded	output voltage	65	70	75	%
Output Undervoltage Fault Propagation Delay	FB forced 2% below trip the	nreshold		10		μs
Output Undervoltage Fault Blanking Time	From SKP/SDN signal goin	g high, clock speed set by R <sub>TIME</sub>		256		clks
Current-Limit Threshold Voltage	CNID LV II IM V	T <sub>A</sub> = +25°C to +85°C	90	100	110	
(Positive, Default)	$GND - LX$ , $ILIM = V_{CC}$	$T_A = 0$ °C to +85°C	85		115	mV
Current-Limit Threshold Voltage	GND - LX	ILIM = 0.5V	35	50	65	
(Positive, Adjustable)		ILIM = REF (2V)	165	200	230	mV
Current-Limit Threshold Voltage (Negative)	LX - GND, ILIM = V <sub>CC</sub>			-117	-95	mV
Current-Limit Threshold Voltage (Zero Crossing)	GND - LX			4		mV
Current-Limit Default Switchover Threshold			3	V <sub>CC</sub> - 1	V <sub>CC</sub> - 0.4	V
Thermal Shutdown Threshold	Hysteresis = 10°C			150		°C
V <sub>CC</sub> Undervoltage Lockout Threshold	Rising edge, hysteresis = this level	20mV, PWM disabled below	4.1		4.4	V
VGATE Lower Trip Threshold	Measured at FB with resp	ect to unloaded output voltage	-12	-10	-8	%
VGATE Upper Trip Threshold	Measured at FB with resp	ect to unloaded output voltage	+8	+10	+12	%
VGATE Propagation Delay	FB forced 2% outside VG/	ATE trip threshold		10		μs
VGATE Output Low Voltage	I <sub>SINK</sub> = 1mA				0.4	V
VGATE Leakage Current	High state, forced to 5.5V				1	μΑ
GATE DRIVERS	•					
DH Gate Driver On-Resistance	BST - LX forced to 5V			1.0	3.5	Ω
DL Gate Driver On-Resistance	DL, high state (pullup)			1.0	3.5	Ω
DE Gale Dilver Officesistatice	DL, low state (pulldown)			0.4	1.0	22
DH Gate-Driver Source/Sink Current	DH forced to 2.5V, BST - LX forced to 5V			1.6		А
DL Gate-Driver Sink Current	DL forced to 2.5V			4		А

### **ELECTRICAL CHARACTERISTICS (continued)**

(Circuit of Figure 1, V+ = 15V,  $V_{CC} = V_{DD} = SKP/\overline{SDN} = 5V$ ,  $V_{OUT} = 1.25V$ ,  $T_A = 0^{\circ}C$  to +85°C, unless otherwise noted.)

PARAMETER	CONDITIONS		MIN	TYP	MAX	UNITS	
DL Gate-Driver Source Current	DL forced to 2.5V		1.6		А		
Dead Time DL rising		35					
Dead Time	me DH rising			26		ns	
LOGIC AND I/O						-	
Logic Input High Voltage	D0-D4, ZMODE, SUS, OVP		2.4			V	
Logic Input Low Voltage	D0-D4, ZMODE, SUS, OVP				0.8	V	
DAC B-Mode Programming Resistor, Low	D0-D4, 0 to 0.4V or 2.6V to 5 ZMODE = V <sub>CC</sub>	5.5V applied through resistor,			1.05	kΩ	
DAC B-Mode Programming Resistor, High	D0–D4, 0 to 0.4V or 2.6V to 5.5V applied through resistor, ZMODE = V <sub>CC</sub>		95			kΩ	
DO DA Dollow /Dolladarowa	I Entering impedance mode L	Pullup		40		1.0	
D0-D4 Pullup/Pulldown		Pulldown		8		kΩ	
Logic Input Current	D0-D4, ZMODE = GND		-1		+1	μΑ	
Logic input Current	ZMODE, SUS, OVP		-1		+1	μΑ	
	For high		V <sub>CC</sub> - 0.4				
4 Level Input Logic Levels	For open		3.15		3.85	V	
(TON, S0, S1)	For REF		1.65		2.35		
	For low				0.5		
SKP/SDN, S0, S1, and TON Input Current	SKP/SDN, S0, S1, TON forced to GND or V <sub>CC</sub>		-3		+3	μA	
	SKP/SDN = logic high (SKIP mode)		2.8		6		
SKP/SDN Input Levels	SKP/SDN = open (PWM mode)		1.4		2.2	V	
SIN /SDIN IIIPUL Levels	SKP/SDN = logic low (shutdown mode)				0.5	<b>v</b>	
	To enable no-fault mode		12		15		
SKP/SDN Float Level	I <sub>SKP/SDN</sub> = 0µA		1.8		2.2	V	

#### **ELECTRICAL CHARACTERISTICS**

(Circuit of Figure 1, V + = 15V,  $V_{CC} = V_{DD} = SKP/\overline{SDN} = 5V$ ,  $V_{OUT} = 1.25V$ ,  $T_A = -40^{\circ}C$  to  $+85^{\circ}C$ , unless otherwise noted.) (Note 2)

PARAMETER	CONDITIONS		MIN	TYP	MAX	UNITS
PWM CONTROLLER						
DC Output Voltage Accuracy	V+ = 4.5V to 28V, includes load	DAC codes from 0.9V to 1.75V	-1.5		+1.5	%
Do Output Voltage Accuracy		DAC codes from 0.6V to 0.875V	-2.0		+2.0	70
	150kHz nominal, R <sub>TIME</sub> = 120kΩ		-8		+8	
TIME Frequency Accuracy	380kHz nominal, $R_{TIME} = 47k\Omega$		-12		+12	%
	38kHz nominal, $R_{TIME} = 470$ kΩ		-12		+12	
	V+ = 5V, FB = 1.2V,	TON = GND (1000kHz)	230		290	
On-Time (Note 1)	V+ = 12V, FB = 1.2V	TON = REF (550kHz)	165		215	no
On-Time (Note 1)		TON = open (300kHz)	320		390	ns
		$TON = V_{CC} (200kHz)$	465		565	1

### **ELECTRICAL CHARACTERISTICS (continued)**

(Circuit of Figure 1, V+ = 15V,  $V_{CC} = V_{DD} = SKP/\overline{SDN} = 5V$ ,  $V_{OUT} = 1.25V$ ,  $T_A = -40^{\circ}C$  to  $+85^{\circ}C$ , unless otherwise noted.) (Note 2)

PARAMETER		CONDITIONS	MIN	TYP	MAX	UNITS
Minimum Off Time (NI-1- 4)	TON = V <sub>CC</sub> , open, or	REF (200kHz, 300kHz, or 550kHz)			500	
Minimum Off-Time (Note 1)	TON = GND (1000kH	Z)			375	ns
BIAS AND REFERENCE						
Quiescent Supply Current (V <sub>CC</sub> )	Measured at V <sub>CC</sub> , FB	forced above the regulation point			1300	μΑ
Quiescent Supply Current (V <sub>DD</sub> )	Measured at V <sub>DD</sub> , FB	forced above the regulation point			5	μΑ
Quiescent Battery Supply Current (V+)					40	μΑ
Shutdown Supply Current (V <sub>CC</sub> )	$SKP/\overline{SDN} = 0$				5	μΑ
Shutdown Supply Current (V <sub>DD</sub> )	SKP/SDN = 0				5	μΑ
Shutdown Battery Supply Current (V+)	SKP/SDN = 0, V <sub>CC</sub> =	V <sub>DD</sub> = 0 or 5V			5	μΑ
Reference Voltage	$V_{CC} = 4.5V \text{ to } 5.5V, r$	o REF load	1.98		2.02	V
FAULT PROTECTION						
Overvoltage Trip Threshold	Measured at FB		1.95		2.05	V
Output Undervoltage Protection Threshold	With respect to unloa	With respect to unloaded output voltage			75	%
Current-Limit Threshold Voltage (Positive, Default)	GND - LX, ILIM = V <sub>C</sub> (		80		115	mV
Current-Limit Threshold Voltage (Positive, Adjustable)	GND - LX	ILIM = 0.5V ILIM = REF (2V)	33 160		65 240	mV
Current-Limit Threshold Voltage (Negative)	LX - GND, ILIM = V <sub>C</sub>		-145		-90	mV
V <sub>CC</sub> Undervoltage Lockout Threshold	Rising edge, hysteresis = 20mV, PWM disabled below this level		4.1		4.4	٧
VGATE Lower Trip Threshold	Measured at FB with respect to unloaded output voltage		-12.5		-7.5	%
VGATE Upper Trip Threshold	Measured at FB with respect to unloaded output voltage		+7.5		+12.5	%
GATE DRIVERS						
DH Gate Driver On-Resistance	BST - LX forced to 5V				3.5	Ω
DL Gate Driver On-Resistance	DL, high state (pullup	))			3.5	Ω
DE Gate Dilver Oil-Hesistatice	DL, low state (pulldov	vn)			1.0	32

### **ELECTRICAL CHARACTERISTICS (continued)**

(Circuit of Figure 1, V + = 15V,  $V_{CC} = V_{DD} = SKP/\overline{SDN} = 5V$ ,  $V_{OUT} = 1.25V$ ,  $T_A = -40^{\circ}C$  to  $+85^{\circ}C$ , unless otherwise noted.) (Note 2)

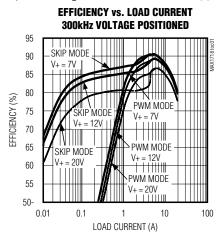
PARAMETER	TER CONDITIONS		TYP	MAX	UNITS
LOGIC AND I/O					
Logic Input High Voltage	D0-D4, ZMODE, SUS, OVP	2.4			V
Logic Input Low Voltage	D0-D4, ZMODE, SUS, OVP			0.8	V
DAC B-Mode Programming Resistor, Low	D0–D4, 0 to 0.4V or 2.6V to 5.5V applied through resistor, ZMODE = $V_{CC}$			1.05	kΩ
DAC B-Mode Programming Resistor, High	D0–D4, 0 to 0.4V or 2.6V to 5.5V applied through resistor, ZMODE = VCC	95			kΩ

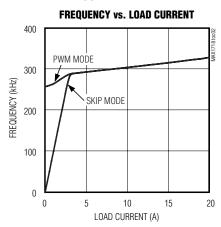
Note 1: On-Time specifications are measured from 50% to 50% at the DH pin, with LX forced to 0V, BST forced to 5V, and a 500pF capacitor from DH to LX to simulate external MOSFET gate capacitance. Actual in-circuit times may be different due to MOSFET switching speeds.

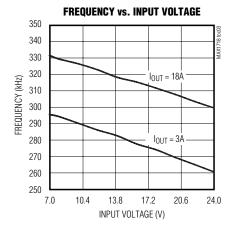
**Note 2:** Specifications to  $T_A = -40^{\circ}C$  are guaranteed by design and not production tested.

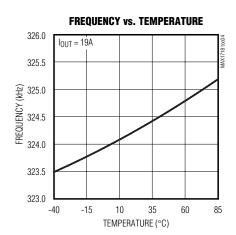
### Typical Operating Characteristics

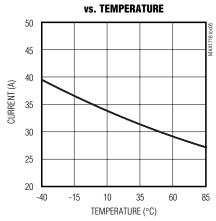
(Circuit of Figure 1, V+ = 12V, VDD = VCC = SKP/SDN = 5V, VOUT = 1.25V, TA = +25°C, unless otherwise noted.)



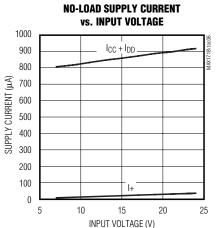






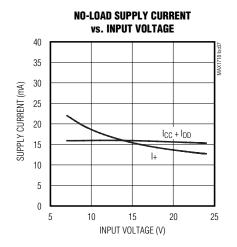


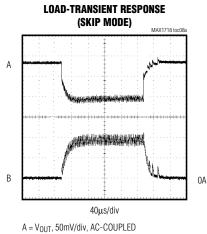
**OUTPUT CURRENT AT CURRENT LIMIT** 

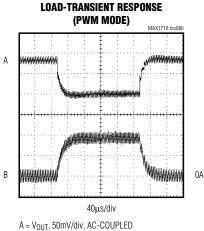


### Typical Operating Characteristics (continued)

(Circuit of Figure 1, V+ = 12V, V<sub>DD</sub> = V<sub>CC</sub> = SKP/SDN = 5V, V<sub>OUT</sub> = 1.25V, T<sub>A</sub> = +25°C, unless otherwise noted.)

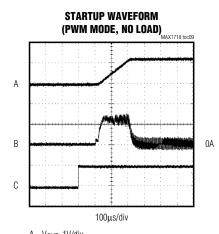




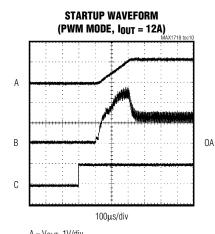


B = INDUCTOR CURRENT, 10A/div

B = INDUCTOR CURRENT, 10A/div

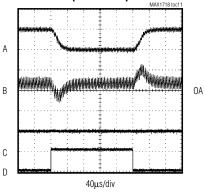


$$\begin{split} A &= V_{OUT}, \, 1V/div \\ B &= INDU\underline{CTO}R \,\, CURRENT, \, 10A/div \end{split}$$
 $C = SKP/\overline{SDN}, 5V/div$ 



$$\begin{split} A &= V_{OUT}, \, 1V/div \\ B &= INDU\underline{CTO}R \,\, CURRENT, \, 10A/div \end{split}$$
 $C = SKP/\overline{SDN}, 5V/div$ 

### **DYNAMIC OUTPUT VOLTAGE TRANSITION** (PWM MODE)



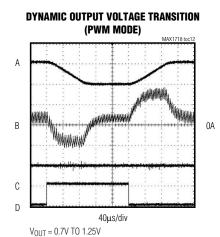
V<sub>OUT</sub> = 1.15V TO 1.25V  $I_{OUT}=3A,\,R_{TIME}=62k\Omega$ 

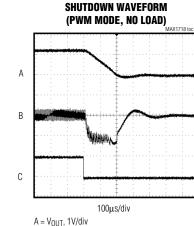
 $A = V_{OUT}$ , 100mV/div, AC-COUPLED B = INDUCTOR CURRENT, 10A/div C = VGATE, 5V/div

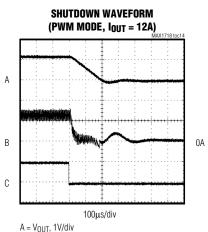
### Typical Operating Characteristics (continued)

0A

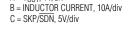
(Circuit of Figure 1, V+ = 12V, V<sub>DD</sub> = V<sub>CC</sub> = SKP/SDN = 5V, V<sub>OUT</sub> = 1.25V, T<sub>A</sub> = +25°C, unless otherwise noted.)

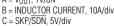


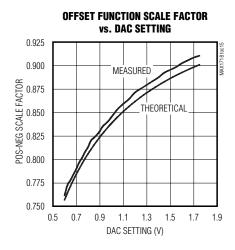


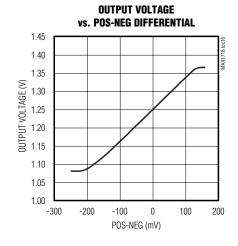


- $I_{OUT} = 3A$ ,  $R_{TIME} = 62k\Omega$  $A = V_{OUT}$ , 500mV/div, AC-COUPLED
- B = INDUCTOR CURRENT, 10A/div
- C = VGATE, 5V/div
- $D = \overline{SUS}$ , 5V/div



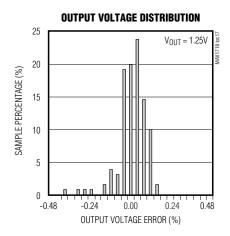


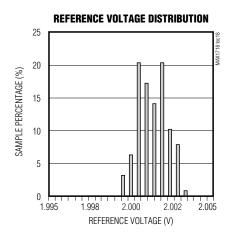




### Typical Operating Characteristics (continued)

(Circuit of Figure 1, V+ = 12V,  $V_{DD} = V_{CC} = SKP/\overline{SDN} = 5V$ ,  $V_{OUT} = 1.25V$ ,  $T_A = +25^{\circ}C$ , unless otherwise noted.)





### **Pin Description**

PIN	NAME	FUNCTION
1	V+	Battery Voltage Sense Connection. Connect V+ to input power source. V+ is used only for PWM one-shot timing. DH on-time is inversely proportional to input voltage over a range of 2V to 28V.
2	SKP/SDN	Combined Shutdown and Skip-Mode Control. Drive SKP/SDN to GND for shutdown. Leave SKP/SDN open for low-noise forced-PWM mode, or drive to V <sub>CC</sub> for pulse-skipping operation. Low-noise forced-PWM mode causes inductor current recirculation at light loads and suppresses pulse-skipping operation. Forcing SKP/SDN to 12V to 15V disables both the overvoltage protection and undervoltage protection circuits and clears the fault latch, with otherwise normal pulse-skipping operation. Do not connect SKP/SDN to > 15V.
3	TIME	Slew-Rate Adjustment Pin. Connect a resistor from TIME to GND to set the internal slew-rate clock. A 470k $\Omega$ to 47k $\Omega$ resistor sets the clock from 38kHz to 380kHz, f <sub>SLEW</sub> = 150kHz × 120k $\Omega$ / R <sub>TIME</sub> .
4	FB	Feedback Input. Connect FB to the junction of the external inductor and the positioning resistor (Figure 1).
5	NEG	Feedback Offset Adjust Negative Input. The output shifts by an amount equal to the difference between POS and NEG multiplied by a scale factor that depends on the DAC codes (see the <i>Integrator Amplifiers/Output Voltage Offsets</i> section). Connect both POS and NEG to REF if the offset function is not used.
6	CC	Integrator Capacitor Connection. Connect a 47pF to 1000pF (47pF typ) capacitor from CC to GND to set the integration time constant (see the <i>Integrator Amplifiers/Output Voltage Offsets</i> section).
7, 8	S0, S1	Suspend-Mode Voltage Select Input. S0 and S1 are four-level digital inputs that select the suspend-mode VID code for the suspend-mode multiplexer inputs. If SUS is high, the suspend-mode VID code is delivered to the DAC (see the <i>Internal Multiplexers (ZMODE/SUS)</i> section).
9	Vcc	Analog Supply Voltage Input for PWM Core. Connect $V_{CC}$ to the system supply voltage (4.5V to 5.5V) with a series $20\Omega$ resistor. Bypass to GND with a 0.22 $\mu$ F (min) capacitor.

### Pin Description (continued)

PIN	NAME	FUNCTION
10	TON	On-Time Selection Control Input. This is a four-level input that sets the K factor (Table 2) to determine DH on-time. Connect TON to the following pins for the indicated operation:  GND = 1000kHz  REF = 550kHz  Open = 300kHz  VCC = 200kHz
11	REF	2V Reference Output. Bypass to GND with 0.22μF (min) capacitor. Can source 50μA for external loads. Loading REF degrades FB accuracy according to the REF load-regulation error.
12	ILIM	Current-Limit Adjustment. The GND - LX current-limit threshold defaults to 100mV if ILIM is connected to V <sub>CC</sub> . In adjustable mode, the current-limit threshold voltage is 1/10th the voltage seen at ILIM over a 0.5V to 3V range. The logic threshold for switchover to the 100mV default value is approximately V <sub>CC</sub> - 1V. Connect ILIM to REF for a fixed 200mV threshold.
13	POS	Feedback Offset Adjust Negative Input. The output shifts by an amount equal to the difference between POS and NEG multiplied by a scale factor that depends on the DAC codes (see the <i>Integrator Amplifiers/Output Voltage Offsets</i> section). Connect both POS and NEG to REF if the offset function is not used.
14	VGATE	Open-Drain Power-Good Output. VGATE is normally high when the output is in regulation. If VFB is not within a ±10% window of the DAC setting, VGATE is asserted low. During DAC code transitions, VGATE is forced high until 1 clock period after the slew-rate controller finishes the transition. VGATE is low during shutdown.
15	GND	Analog and Power Ground. Also connects to the current-limit comparator.
16	DL	Low-Side Gate Driver Output. DL swings GND to V <sub>DD</sub> .
17	$V_{DD}$	Supply Voltage Input for the DL Gate Driver, 4.5V to 5.5V. Bypass to GND with a 1µF capacitor.
18	SUS	Suspend-Mode Control Input. When SUS is high, the suspend-mode VID code, as programmed by S0 and S1, is delivered to the DAC. Connect SUS to GND if the Suspend-mode multiplexer is not used (see the <i>Internal Multiplexers (ZMODE/SUS)</i> section).
19	ZMODE	Performance-Mode MUX Control Input. If SUS is low, ZMODE selects between two different VID DAC codes. If ZMODE is low, the VID DAC code is set by the logic-level voltages on D0–D4. On the rising edge of ZMODE, during power-up with ZMODE high, or on the falling edge of SUS when ZMODE is high, the VID DAC code is determined by the impedance at D0–D4 (see the <i>Internal Multiplexers (ZMODE/SUS)</i> section).
20	OVP	Overvoltage Protection Control Input. Connect $\overline{\text{OVP}}$ low to enable overvoltage protection. Connect $\overline{\text{OVP}}$ high to disable overvoltage protection. The overvoltage trip threshold is approximately 2V. The state of $\overline{\text{OVP}}$ does not affect output undervoltage fault protection or thermal shutdown.
21–25	D4-D0	VID DAC Code Inputs. D0 is the LSB, and D4 is the MSB of the internal 5-bit VID DAC (Table 3). If ZMODE is low, D0–D4 are high-impedance digital inputs, and the VID DAC code is set by the logic-level voltages on D0–D4. On the rising edge of ZMODE, during power-up with ZMODE high, or on the falling edge of SUS when ZMODE is high, the VID DAC code is determined by the impedance at D0–D4 as follows: Logic low = source impedance is $\leq 1 k\Omega + 5\%$ . Logic high = source impedance is $\geq 100 k\Omega - 5\%$ .
26	BST	Boost Flying Capacitor Connection. Connect BST to the external boost diode and capacitor as shown in Figure 1. An optional resistor in series with BST allows the DH pullup current to be adjusted (Figure 8).
27	LX	Inductor Connection. LX is the internal lower supply rail for the DH high-side gate driver. It also connects to the current-limit comparator and the skip-mode zero-crossing comparator.
28	DH	High-Side Gate-Driver Output. DH swings LX to BST.

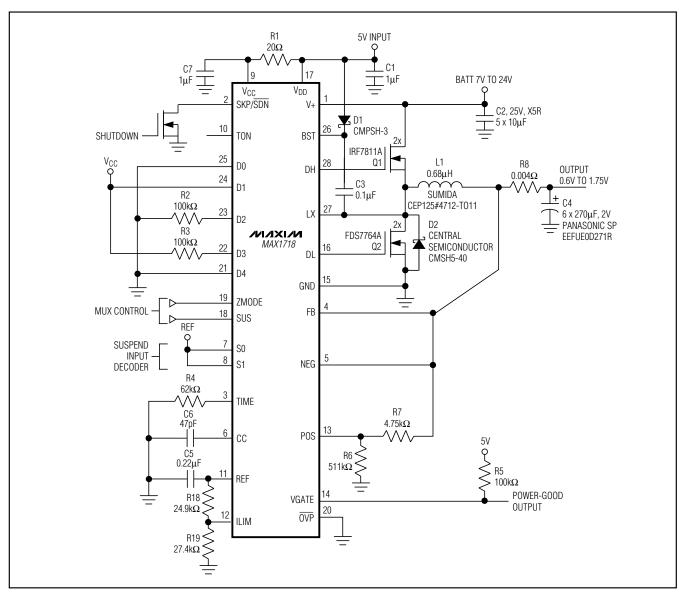


Figure 1. Standard Application Circuit

**Table 1. Component Suppliers** 

MANUFACTURER	USA PHONE	FACTORY FAX
Central Semiconductor	entral Semiconductor 516-435-1110	
Dale-Vishay	402-564-3131	402-563-6418
Fairchild	408-721-2181	408-721-1635
International Rectifier	310-322-3331	310-322-3332
Kemet	408-986-0424	408-986-1442
Motorola	602-303-5454	602-994-6430
Nihon	847-843-7500	847-843-2798
Panasonic	714-373-7939	714-373-7183
Taiyo Yuden	408-573-4150	408-573-4159
TDK	847-390-4373	847-390-4428
Toko	800-745-8656	408-943-9790
Sanyo	619-661-6835	619-661-1055
SGS-Thomson	617-259-0300	617-259-9442
Sumida	708-956-0666	708-956-0702
Zetex	516-543-7100	516-864-7630

### **Detailed Description**

#### 5V Bias Supply (VCC and VDD)

The MAX1718 requires an external 5V bias supply in addition to the battery. Typically, this 5V bias supply is the notebook's 95% efficient 5V system supply. Keeping the bias supply external to the IC improves efficiency and eliminates the cost associated with the 5V linear regulator that would otherwise be needed to supply the PWM circuit and gate drivers. If stand-alone capability is needed, the 5V supply can be generated with an external linear regulator.

The 5V bias supply must provide  $V_{CC}$  (PWM controller) and  $V_{DD}$  (gate-drive power), so the maximum current drawn is:

$$IBIAS = ICC + f(QG1 + QG2) = 10mA to 40mA (typ)$$

where I<sub>CC</sub> is  $800\mu$ A (typ), f is the switching frequency, and Q<sub>G1</sub> and Q<sub>G2</sub> are the MOSFET data sheet total gate-charge specification limits at V<sub>GS</sub> = 5V.

V+ and V<sub>DD</sub> can be tied together if the input power source is a fixed 4.5V to 5.5V supply. If the 5V bias supply is powered up prior to the battery supply, the enable signal (SKP/SDN going from low to high or open) must be delayed until the battery voltage is present to ensure startup.

### Free-Running, Constant On-Time PWM Controller with Input Feed-Forward

The Quick-PWM control architecture is a pseudofixed-frequency, constant-on-time current-mode type with voltage feed-forward (Figure 2). This architecture relies on the output filter capacitor's ESR to act as the current-sense resistor, so the output ripple voltage provides the PWM ramp signal. The control algorithm is simple: the high-side switch on-time is determined solely by a one-shot whose period is inversely proportional to input voltage and directly proportional to output voltage. Another one-shot sets a minimum off-time (400ns typ). The on-time one-shot is triggered if the error comparator is low, the low-side switch current is below the current-limit threshold, and the minimum off-time one-shot has timed out.

#### **On-Time One-Shot (TON)**

The heart of the PWM core is the one-shot that sets the high-side switch on-time. This fast, low-jitter, adjustable one-shot includes circuitry that varies the on-time in response to battery and output voltage. The high-side switch on-time is inversely proportional to the battery voltage as measured by the V+ input, and proportional to the output voltage. This algorithm results in a nearly constant switching frequency despite the lack of a fixed-frequency clock generator. The benefits of a constant switching frequency are twofold: first, the frequency can be selected to avoid noise-sensitive regions such as the 455kHz IF band; second, the inductor ripple-current operating point remains relatively constant, resulting in easy design methodology and predictable output voltage ripple.

On-Time = 
$$K (V_{OUT} + 0.075V) / V_{IN}$$

where K is set by the TON pin-strap connection and 0.075V is an approximation to accommodate the expected drop across the low-side MOSFET switch (Table 2).

The on-time one-shot has good accuracy at the operating points specified in the *Electrical Characteristics table* (±10% at 200kHz and 300kHz, ±12% at 550kHz and 1000kHz). On-times at operating points far removed from the conditions specified in the *Electrical Characteristics* table can vary over a wider range. For example, the 1000kHz setting will typically run about 10% slower with inputs much greater than +5V due to the very short ontimes required.

On-times translate only roughly to switching frequencies. The on-times guaranteed in the *Electrical Characteristics* table are influenced by switching delays in the

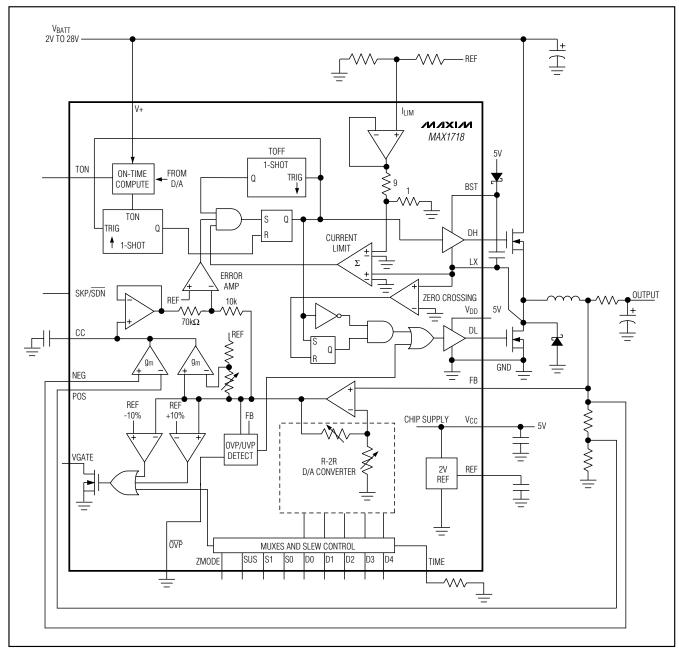


Figure 2. Functional Diagram

**Table 2. Approximate K-Factor Errors** 

TON	TON FREQUENCY	K-FACTOR	APPROXIMATE K-	MIN RECOMMENDED VBATT AT	
SETTING	(kHZ)	(µs)	FACTOR ERROR (%)	V <sub>OUT</sub> = 1.25V (V)	V <sub>OUT</sub> = 1.75V (V)
V <sub>CC</sub>	200	5	±10	1.7	2.3
OPEN	300	3.3	±10	1.8	2.5
REF	550	1.8	±12.5	2.6	3.5
GND	1000	1.0	±12.5	3.6	4.9

external high-side MOSFET. Resistive losses, including the inductor, both MOSFETs, output capacitor ESR, and PC board copper losses in the output and ground tend to raise the switching frequency at higher output currents. Also, the dead-time effect increases the effective on-time, reducing the switching frequency. It occurs only in PWM mode (SKP/SDN = open) and during dynamic output voltage transitions when the inductor current reverses at light or negative load currents. With reversed inductor current, the inductor's EMF causes LX to go high earlier than normal, extending the on-time by a period equal to the DH-rising dead time.

For loads above the critical conduction point, where the dead-time effect is no longer a factor, the actual switching frequency is:

$$f = \frac{(V_{OUT} + V_{DROP1})}{t_{ON}(V_{IN} + V_{DROP1} - V_{DROP2})}$$

where  $V_{DROP1}$  is the sum of the parasitic voltage drops in the inductor discharge path, including synchronous rectifier, inductor, and PC board resistances;  $V_{DROP2}$  is the sum of the parasitic voltage drops in the inductor charge path, including high-side switch, inductor, and PC board resistances; and  $t_{ON}$  is the on-time calculated by the MAX1718.

### Integrator Amplifiers/Output Voltage Offsets

Two transconductance integrator amplifiers provide a fine adjustment to the output regulation point. One amplifier forces the DC average of the feedback voltage to equal the VID DAC setting. The second amplifier is used to create small positive or negative offsets from the VID DAC setting, using the POS and NEG pins.

The integrator block has the ability to lower the output voltage by 8% and raise it by 8%. For each amplifier, the differential input voltage range is at least ±80mV total, including DC offset and AC ripple. The two amplifiers' outputs are directly summed inside the chip, so the integration time constant can be set easily with one capacitor at the CC pin. Use a capacitor value of 47pF

to 1000pF (47pF typ). The  $g_m$  of each amplifier is 160µmho (typ).

The POS/NEG amplifier is used to add small offsets to the VID DAC setting or to correct for voltage drops. To create an output offset, bias POS and NEG to a voltage (typically Vout or REF) within their common-mode range, and offset them from one another with a resistive divider (Figures 3 and 4). If Vpos is higher than Vneg, then the output is shifted in the positive direction. If Vneg is higher than Vpos, then the output is shifted in the negative direction. The amount of output offset is less than the difference from POS to NEG by a scale factor that varies with the VID DAC setting as shown in Table 3. The common-mode range of POS and NEG is 0.4V to 2.5V.

For applications that require multiple offsets, an external multiplexer can be used to select various resistor values (Figure 5).

Both the integrator amplifiers can be disabled by connecting NEG to  $\ensuremath{\text{V}_{\text{CC}}}.$ 

#### Forced-PWM Mode (SKP/SDN Open)

The low-noise forced-PWM mode (SKP/SDN open) disables the zero-crossing comparator, allowing the inductor current to reverse at light loads. This causes the low-side gate-drive waveform to become the complement of the high-side gate-drive waveform. The benefit of forced-PWM mode is to keep the switching frequency fairly constant, but it comes at a cost: the no-load battery current can be 10mA to 40mA, depending on the external MOSFETs and switching frequency.

Forced-PWM mode is required during downward output voltage transitions. The MAX1718 uses PWM mode during all transitions, but only while the slew-rate controller is active. Due to voltage positioning, when a transition uses high negative inductor current, the output voltage does not settle to its final intended value until well after the slew-rate controller terminates. Because of this it is possible, at very high negative slew currents, for the output to end up high enough to cause VGATE to go low.

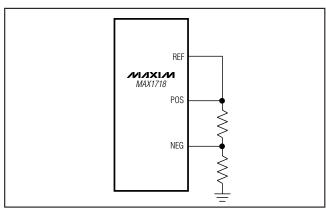


Figure 3. Resistive Divider from REF

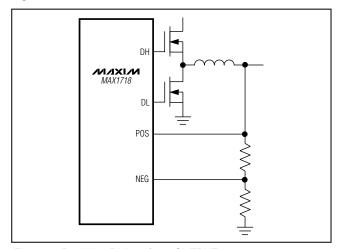


Figure 4. Resistive Divider from OUTPUT

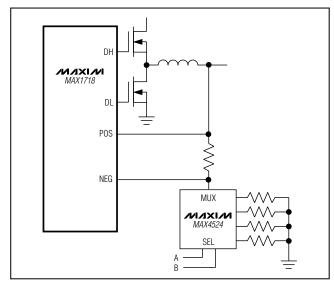


Figure 5. Programmable Offset Voltage

Thus, it is necessary to use forced PWM mode during all negative transitions. Most applications should use PWM mode exclusively, although there is some benefit to using skip mode while in the low-power suspend state (see the *Using Skip Mode During Suspend (SKP/SDN = VCC)* section.)

#### **Automatic Pulse-Skipping Switchover**

In skip mode (SKP/SDN high), an inherent automatic switchover to PFM takes place at light loads (Figure 6). This switchover is effected by a comparator that truncates the low-side switch on-time at the inductor current's zero crossing. This mechanism causes the threshold between pulse-skipping PFM and nonskipping PWM operation to coincide with the boundary between continuous and discontinuous inductor-current operation. The load-current level at which PFM/PWM crossover occurs, ILOAD(SKIP), is equal to 1/2 the peak-to-peak ripple current, which is a function of the inductor value (Figure 6). For a battery range of 7V to 24V, this threshold is relatively constant, with only a minor dependence on battery voltage:

$$I_{LOAD(SKIP)} \approx \frac{K \times V_{OUT}}{2 \times L} \times \frac{V_{BATT} - V_{OUT}}{V_{BATT}}$$

where K is the on-time scale factor (Table 2). For example, in the standard application circuit this becomes:

$$\frac{3.3\mu s \times 1.25V}{2 \times 0.68\mu H} \times \frac{12V - 1.25V}{12V} = 2.7A$$

The crossover point occurs at a lower value if a swinging (soft-saturation) inductor is used.

The switching waveforms may appear noisy and asynchronous when light loading causes pulse-skipping operation, but this is a normal operating condition that results in high light-load efficiency. Trade-offs in PFM noise vs. light-load efficiency are made by varying the inductor value. Generally, low inductor values produce a broader efficiency vs. load curve, while higher values result in higher full-load efficiency (assuming that the coil resistance remains fixed) and less output voltage ripple. Penalties for using higher inductor values include larger physical size and degraded load-transient response, especially at low input voltage levels.

#### **Current-Limit Circuit**

The current-limit circuit employs a unique "valley" current-sensing algorithm that uses the on-resistance of the low-side MOSFET as a current-sensing element. If the current-sense signal is above the current-limit threshold, the PWM is not allowed to initiate a new cycle

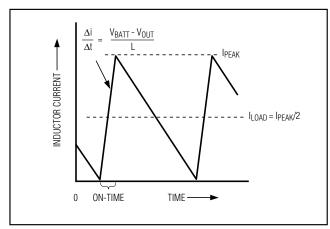


Figure 6. Pulse-Skipping/Discontinuous Crossover Point

(Figure 7). The actual peak current is greater than the current-limit threshold by an amount equal to the inductor ripple current. Therefore, the exact current-limit characteristic and maximum load capability are a function of the MOSFET on-resistance, inductor value, and battery voltage. The reward for this uncertainty is robust, lossless overcurrent sensing. When combined with the undervoltage protection circuit, this current-limit method is effective in almost every circumstance.

There is also a negative current limit that prevents excessive reverse inductor currents when V<sub>OUT</sub> is sinking current. The negative current-limit threshold is set to approximately 120% of the positive current limit, and therefore tracks the positive current limit when ILIM is adjusted.

The current-limit threshold is adjusted with an external resistor-divider at ILIM. The current-limit threshold voltage adjustment range is from 50mV to 300mV. In the adjustable mode, the current-limit threshold voltage is precisely 1/10th the voltage seen at ILIM. The threshold defaults to 100mV when ILIM is connected to VCC. The logic threshold for switchover to the 100mV default value is approximately VCC - 1V.

The adjustable current limit accommodates MOSFETs with a wide range of on-resistance characteristics (see the *Design Procedure* section). For a high-accuracy current-limit application, see Figure 16.

Carefully observe the PC board layout guidelines to ensure that noise and DC errors don't corrupt the current-sense signals seen by LX and GND. Place the IC close to the low-side MOSFET with short, direct traces, making a Kelvin sense connection to the source and drain terminals.

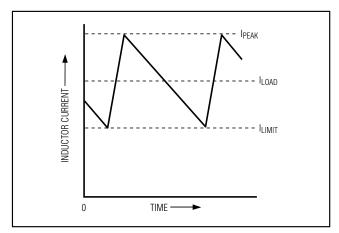


Figure 7. "Valley" Current-Limit Threshold Point

### **MOSFET Gate Drivers (DH, DL)**

The DH and DL drivers are optimized for driving moderate-sized high-side and larger low-side power MOSFETs. This is consistent with the low duty factor seen in the notebook CPU environment, where a large VBATT - VOUT differential exists. An adaptive dead-time circuit monitors the DL output and prevents the high-side FET from turning on until DL is fully off. There must be a low-resistance, low-inductance path from the DL driver to the MOSFET gate for the adaptive dead-time circuit to work properly. Otherwise, the sense circuitry in the MAX1718 will interpret the MOSFET gate as "off" while there is actually still charge left on the gate. Use very short, wide traces measuring 10 to 20 squares (50 to 100 mils wide if the MOSFET is 1 inch from the MAX1718).

The dead time at the other edge (DH turning off) is determined by a fixed 35ns (typ) internal delay.

The internal pulldown transistor that drives DL low is robust, with a  $0.4\Omega$  (typ) on-resistance. This helps prevent DL from being pulled up during the fast rise-time of the inductor node, due to capacitive coupling from the drain to the gate of the low-side synchronous-rectifier MOSFET. However, for high-current applications, you might still encounter some combinations of high- and low-side FETs that will cause excessive gate-drain coupling, which can lead to efficiency-killing, EMI-producing shoot-through currents. This is often remedied by adding a resistor in series with BST, which increases the turn-on time of the high-side FET without degrading the turn-off time (Figure 8).

#### **POR**

Power-on reset (POR) occurs when V<sub>CC</sub> rises above approximately 2V, resetting the fault latch and preparing the PWM for operation. V<sub>CC</sub> undervoltage lockout

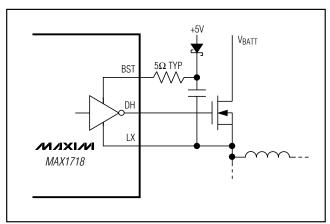


Figure 8. Reducing the Switching-Node Rise Time

(UVLO) circuitry inhibits switching, forces VGATE low, and forces the DL gate driver high (to enforce output overvoltage protection). When V<sub>CC</sub> rises above 4.2V, the DAC inputs are sampled and the output voltage begins to slew to the DAC setting.

For automatic startup, the battery voltage should be present before V<sub>CC</sub>. If the MAX1718 attempts to bring the output into regulation without the battery voltage present, the fault latch will trip. The SKP/SDN pin can be toggled to reset the fault latch.

#### Shutdown

When SKP/ $\overline{\text{SDN}}$  goes low, the MAX1718 enters low-power shutdown mode. VGATE goes low immediately. The output voltage ramps down to 0V in 25mV steps at the clock rate set by R<sub>TIME</sub>. When the DAC reaches the 0V setting, DL goes high, DH goes low, the reference is turned off, and the supply current drops to about 2 $\mu$ A.

When SKP/SDN goes high or floats, the reference powers up, and after the reference UVLO is passed, the DAC target is evaluated and switching begins. The slew-rate controller ramps up from 0V in 25mV steps to the currently selected code value (based on ZMODE and SUS). There is no traditional soft-start (variable current limit) circuitry, so full output current is available immediately. VGATE goes high after the slew-rate controller has terminated and the output voltage is in regulation.

#### UVLO

If  $V_{CC}$  drops low enough to trip the UVLO comparator, it is assumed that there is not enough supply voltage to make valid decisions. To protect the output from overvoltage faults, DL is forced high in this mode. This will force the output to GND, but it will not use the slew-rate controller. This results in large negative inductor current

and possibly small negative output voltages. If  $V_{\rm CC}$  is likely to drop in this fashion, the output can be clamped with a Schottky diode to GND to reduce the negative excursion.

#### **DAC Inputs D0-D4**

The digital-to-analog converter (DAC) programs the output voltage. It typically receives a preset digital code from the CPU pins, which are either hard-wired to GND or left open-circuit. They can also be driven by digital logic, general-purpose I/O, or an external mux. Do not leave D0-D4 floating-use  $1M\Omega$  or less pullups if the inputs may float. D0-D4 can be changed while the SMPS is active, initiating a transition to a new output voltage level. If this mode of DAC control is used, connect ZMODE and SUS low. Change D0-D4 together, avoiding greater than 1µs skew between bits. Otherwise, incorrect DAC readings may cause a partial transition to the wrong voltage level, followed by the intended transition to the correct voltage level, lengthening the overall transition time. The available DAC codes and resulting output voltages (Table 3) are compatible with IMVP-II specification.

#### **Internal Multiplexers (ZMODE, SUS)**

The MAX1718 has two unique internal VID input multiplexers (muxes) that can select one of three different VID DAC code settings for different processor states. Depending on the logic level at SUS, the Suspend (SUS) mode mux selects the VID DAC code settings from either the ZMODE mux or the S0/S1 input decoder. The ZMODE mux selects one of the two VID DAC code settings from the D0–D4 pins, based on either voltage on the pins or the output of the impedance decoder (Figure 9).

When SUS is high, the Suspend mode mux selects the VID DAC code settings from the S0/S1 input decoder. The outputs of the decoder are determined by inputs S0 and S1 (Table 4).

When SUS is low, the Suspend mode mux selects the output of the ZMODE mux. Depending on the logic level at ZMODE, the ZMODE mux selects the VID DAC code settings using either the voltage on D0–D4 or the output of the impedance decoder (Table 5).

If ZMODE is low, the logic-level voltages on D0-D4 set the VID DAC settings. This is called Logic mode. In this mode, the inputs are continuously active and can be dynamically changed by external logic. The Logic mode VID DAC code setting is typically used for the Battery mode state, and the source of this code is sometimes the VID pins of the CPU with suitable pullup resistors.

Table 3. Output Voltage vs. DAC Codes

D4	D3	D2	D1	D0	OUTPUT VOLTAGE (V)	POS/NEG SCALE FACTOR
0	0	0	0	0	1.75	0.90
0	0	0	0	1	1.70	0.90
0	0	0	1	0	1.65	0.90
0	0	0	1	1	1.60	0.89
0	0	1	0	0	1.55	0.89
0	0	1	0	1	1.50	0.89
0	0	1	1	0	1.45	0.88
0	0	1	1	1	1.40	0.88
0	1	0	0	0	1.35	0.88
0	1	0	0	1	1.30	0.87
0	1	0	1	0	1.25	0.87
0	1	0	1	1	1.20	0.86
0	1	1	0	0	1.15	0.86
0	1	1	0	1	1.10	0.85
0	1	1	1	0	1.05	0.85
0	1	1	1	1	1.00	0.84
1	0	0	0	0	0.975	0.84
1	0	0	0	1	0.950	0.83
1	0	0	1	0	0.925	0.83
1	0	0	1	1	0.900	0.82
1	0	1	0	0	0.875	0.82
1	0	1	0	1	0.850	0.82
1	0	1	1	0	0.825	0.81
1	0	1	1	1	0.800	0.81
1	1	0	0	0	0.775	0.80
1	1	0	0	1	0.750	0.80
1	1	0	1	0	0.725	0.79
1	1	0	1	1	0.700	0.78
1	1	1	0	0	0.675	0.78
1	1	1	0	1	0.650	0.77
1	1	1	1	0	0.625	0.76
1	1	1	1	1	0.600	0.76

18 \_\_\_\_\_\_ NIXI/N

On the rising edge of ZMODE, during power-up with ZMODE high or on the falling edge of SUS when ZMODE is high, the impedances at D0-D4 are sampled by the impedance decoder to see if a large resistance is in series with the pin. This is called Impedance mode. If the voltage level on the pin is a logic low, an internal switch connects the pin to an internal  $26k\Omega$ pullup for about 4µs to see if the pin voltage can be forced high (Figure 10). If the pin voltage can be pulled to a logic high, the impedance is considered high and so is the Impedance mode logic state. Similarly, if the voltage level on the pin is a logic high, an internal switch connects the pin to an internal  $8k\Omega$  pulldown to see if the pin voltage can be forced low. If so, the pin is high impedance and its Impedance mode logic state is high. In either sampling condition, if the pin's logic level does not change, the pin is determined to be low impedance and the Impedance mode logic state is low.

A high pin impedance (and logic high) is  $100 k\Omega$  or greater, and a low impedance (and logic low) is  $1k\Omega$  or less. The *Electrical Characteristics* table guaranteed levels for these impedances are  $95 k\Omega$  and  $1.05 k\Omega$  to allow the use of standard  $100 k\Omega$  and  $1k\Omega$  resistors with 5% tolerance.

#### Using the ZMODE Mux

There are many ways to use the versatile ZMODE mux. The preferred method will depend on when and how the VID DAC codes for the various states are determined. If the output voltage codes are fixed at PC board design time, program both codes with a simple combination of pin-strap connections and series resistors (Figure 11). If the output voltage codes are chosen during PC board assembly, both codes can be independently programmed with resistors (Figure 12). This

**Table 4. Suspend Mode DAC Codes** 

S1	S0	OUTPUT VOLTAGE (V)
GND	GND	0.975
GND	REF	0.950
GND	OPEN	0.925
GND	Vcc	0.900
REF	GND	0.875
REF	REF	0.850
REF	OPEN	0.825
REF	VCC	0.800
OPEN	GND	0.775
OPEN	REF	0.750
OPEN	OPEN	0.725
OPEN	Vcc	0.700
Vcc	GND	0.675
Vcc	REF	0.650
Vcc	OPEN	0.625
V <sub>C</sub> C	V <sub>C</sub> C	0.600

matrix of 10 resistor-footprints can be programmed to all possible Logic mode and Impedance mode code combinations with only 5 resistors.

Often the CPU pins provide one set of codes that are typically used with pullup resistors to provide the Logic mode VID code, and resistors in series with D0–D4 set the Impedance mode code. Since some of the CPU's VID pins may float, the open-circuit pins can present a problem for the ZMODE mux's Impedance mode. For the Impedance mode to work, any pins intended to be

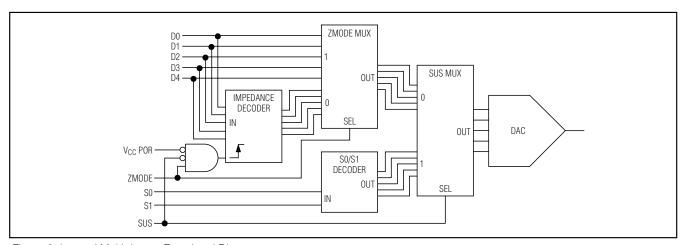


Figure 9. Internal Multiplexers Functional Diagram

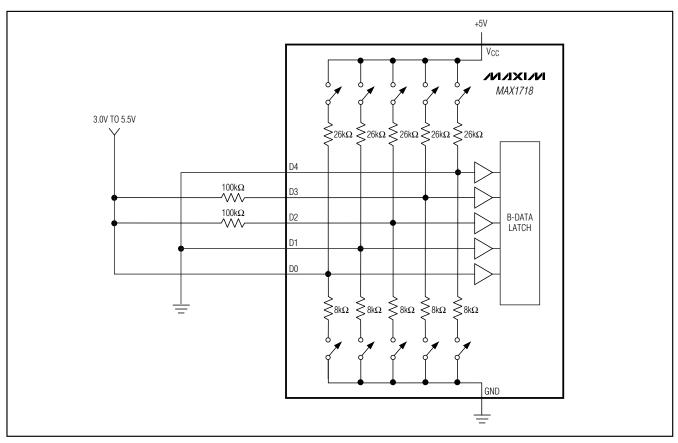


Figure 10. Internal Mux Impedance-Mode Data Test and Latch

low during Impedance mode must appear to be low impedance, at least for the 4µs sampling interval.

This can be achieved in several ways, including the following two (Figure 13). By using low-impedance pullup resistors with the CPU's VID pins, each pin provides the low impedance needed for the mux to correctly interpret the Impedance mode setting. Unfortunately, the low resistances cause several mA quiescent currents for each of the CPU's grounded VID pins. This quiescent current can be avoided by taking advantage of the fact that D0-D4 need only appear low impedance briefly, not necessarily on a continuous DC basis. Highimpedance pullups can be used if they are bypassed with a large enough capacitance to make them appear low impedance for the 4us sampling interval. As noted in Figure 13, 4.7nF capacitors allow the inputs to appear low impedance even though they are pulled up with large-value resistors. Each sampling depletes some charge from the 4.7nF capacitors. A minimum

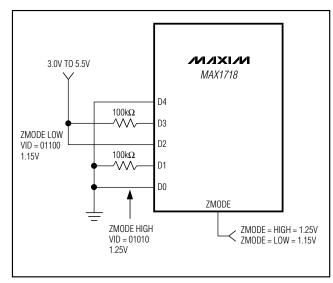


Figure 11. Using the Internal Mux with Hard-Wired Logic-Mode and Impedance-Mode DAC Codes

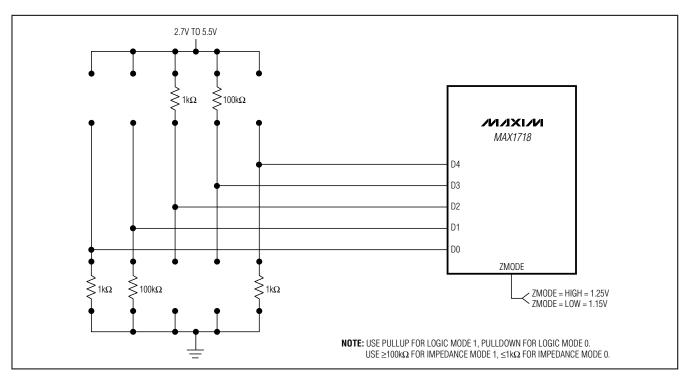


Figure 12. Using the Internal Mux with Both VID Codes Resistor Programmed

interval of 2  $\times$  R<sub>PULLUP</sub>  $\times$  4.7nF is recommended between ZMODE samples.

In some cases, it is desirable to determine the Impedance mode code during system boot so that several processor types can be used without hardware modifications. Figure 14 shows one way to implement this function. The desired code is determined by the system BIOS and programmed into one register of the MAX1609 using the SMBus™ serial interface. The MAX1609's other register is left in its power-up state (all outputs high impedance). When SMBSUS is low, the outputs are high impedance and do not affect the Logic-mode VID code setting. When SMBSUS is high, the programmed register is selected, and the MAX1609 forces a low impedance on the appropriate VID input pins. The ZMODE signal is delayed relative to the SMB-SUS pin because the VID pins that are pulled low by the MAX1609 take significant time to rise when they are released. One additional benefit of using the MAX1609 for this application is that the application uses only five of the MAX1609's high-voltage, open-drain outputs. The other three outputs can be used for other purposes.

**Table 5. DAC Mux Operation** 

ZMODE	sus	OUTPUT VOLTAGE DETERMINED BY:
GND	GND	Logic Level of D0-D4
V <sub>CC</sub> GND		Impedance of D0-D4
X VCC		Logic Levels of S0, S1

### **Output Voltage Transition Timing**

The MAX1718 is designed to perform output voltage transitions in a controlled manner, automatically minimizing input surge currents. This feature allows the circuit designer to achieve nearly ideal transitions, guaranteeing just-in-time arrival at the new output voltage level with the lowest possible peak currents for a given output capacitance. This makes the IC ideal for IMVP-II CPUs.

IMVP-II CPUs operate at two distinct clock frequencies and require three distinct VID settings. When transitioning from one clock frequency to the other, the CPU first goes into a low-power state, then the output voltage and clock frequency are changed. The change must be accomplished in 100µs or the system may halt.

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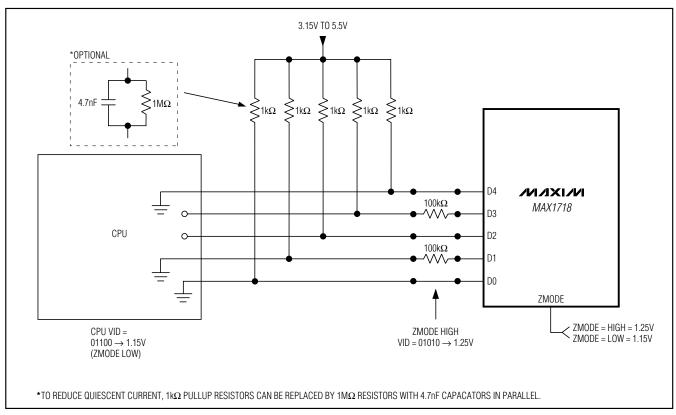


Figure 13. Using the Internal Mux with CPU Driving the Logic-Mode VID Code

At the beginning of an output voltage transition, the MAX1718 blanks the VGATE output, preventing it from going low. VGATE remains blanked during the transition and is re-enabled when the slew-rate controller has set the internal DAC to the final value and one additional slew-rate clock period has passed. The slew-rate clock frequency (set by resistor R<sub>TIME</sub>) must be set fast enough to ensure that the longest required transition is completed within the allowed 100µs.

The output voltage transition is performed in 25mV steps, preceded by a delay and followed by one additional clock period. The total time for a transition depends on RTIME, the voltage difference, and the accuracy of the MAX1718's slew-rate clock, and is not dependent on the total output capacitance. The greater the output capacitance, the higher the surge current required for the transition. The MAX1718 will automatically control the current to the minimum level required to complete the transition in the calculated time, as long as the surge current is less than the current limit set by ILIM. The transition time is given by:

$$\leq \left\lceil \frac{1}{f_{SLEW}} \times \frac{V_{OLD} - V_{NEW}}{25mV} \right\rceil + T_{DELAY}$$

where  $f_{SLEW}=150 kHz \times 120 k\Omega$  / RTIME, VOLD is the original DAC setting, V<sub>NEW</sub> is the new DAC setting, and T<sub>DELAY</sub> ranges from zero to a maximum of 2/f<sub>SLEW</sub>. See Time Frequency Accuracy in the *Electrical Characteristics* table for f<sub>SLEW</sub> accuracy.

The practical range of R<sub>TIME</sub> is  $47k\Omega$  to  $470k\Omega$ , corresponding to 2.6µs to 26µs per 25mV step. Although the DAC takes discrete 25mV steps, the output filter makes the transitions relatively smooth. The average inductor current required to make an output voltage transition is:

$$I_L \cong C_{OUT} \times 25 \text{mV} \times f_{SLEW}$$

#### **Output Overvoltage Protection**

The overvoltage protection (OVP) circuit is designed to protect the CPU against a shorted high-side MOSFET by drawing high current and blowing the battery fuse. The output voltage is continuously monitored for over-

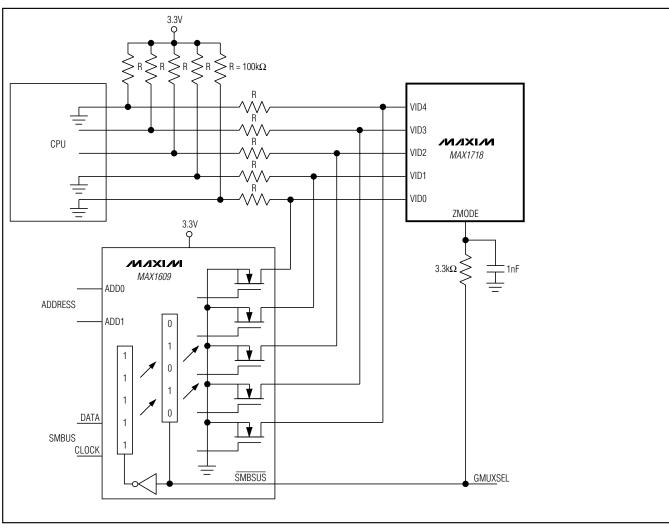


Figure 14. Using the ZMODE Multiplexer

voltage. If the output is more than 2V, OVP is triggered and the circuit shuts down. The DL low-side gate-driver output is then latched high until SKP/SDN is toggled or V<sub>CC</sub> power is cycled below 1V. This action turns on the synchronous-rectifier MOSFET with 100% duty and, in turn, rapidly discharges the output filter capacitor and forces the output to ground. If the condition that caused the overvoltage (such as a shorted high-side MOSFET) persists, the battery fuse will blow. DL is also kept high continuously when V<sub>CC</sub> UVLO is active, as well as in shutdown mode (Table 6).

Overvoltage protection can be defeated with a logic high on  $\overline{\text{OVP}}$  or through the NO FAULT test mode (see the NO FAULT Test Mode section).

#### **Output Undervoltage Shutdown**

The output UVP function is similar to foldback current limiting, but employs a timer rather than a variable current limit. If the MAX1718 output voltage is under 70% of the nominal value, the PWM is latched off and won't restart until VCC power is cycled or SKP/SDN is toggled. To allow startup, UVP is ignored during the undervoltage fault-blanking time (the first 256 cycles of the slew rate after startup).

UVP can be defeated through the NO FAULT test mode (see the NO FAULT Test Mode section).

**Table 6. Operating Mode Truth Table** 

SKP/SDN	DL	MODE	COMMENT
GND	High	Shutdown	Low-power shutdown state. DL is forced to $V_{DD}$ , enforcing OVP. $I_{CC}$ + $I_{DD}$ = $2\mu A$ typ.
12V to 15V	Switching	No Fault	Test mode with faults disabled and fault latches cleared, including thermal shutdown. Otherwise, normal operation, with automatic PWM/PFM switchover for pulse-skipping at light loads.
Open	Switching	Run (PWM, low noise)	Low-noise operation with no automatic switchover. Fixed-frequency PWM action is forced regardless of load. Inductor current reverses at light load levels.
Vcc	Switching	Run (PFM/PWM)	Operation with automatic PWM/PFM switchover for pulse-skipping at light loads.
V <sub>CC</sub> or Open	High	Fault	Fault latch has been set by OVP, UVP, or thermal shutdown. Device will remain in FAULT mode until V <sub>CC</sub> power is cycled or SKP/SDN is forced low.

#### **NO FAULT Test Mode**

The over/undervoltage protection features can complicate the process of debugging prototype breadboards since there are (at most) a few milliseconds in which to determine what went wrong. Therefore, a test mode is provided to disable the OVP, UVP, and thermal shutdown features, and clear the fault latch if it has been set. The PWM operates as if SKP/SDN were high (SKIP mode). The NO FAULT test mode is entered by forcing 12V to 15V on SKP/SDN.

### Design Procedure

Firmly establish the input voltage range and maximum load current before choosing a switching frequency and inductor operating point (ripple-current ratio). The primary design trade-off lies in choosing a good switching frequency and inductor operating point, and the following four factors dictate the rest of the design:

- Input Voltage Range. The maximum value (V<sub>IN(MAX)</sub>) must accommodate the worst-case high AC adapter voltage. The minimum value (V<sub>IN(MIN)</sub>) must account for the lowest battery voltage after drops due to connectors, fuses, and battery selector switches. If there is a choice at all, lower input voltages result in better efficiency.
- 2) Maximum Load Current. There are two values to consider. The peak load current (I<sub>LOAD(MAX)</sub>) determines the instantaneous component stresses and filtering requirements, and thus drives output capacitor selection, inductor saturation rating, and the design of the current-limit circuit. The continuous load current (I<sub>LOAD</sub>) determines the thermal stresses and thus drives the selection of input capacitors,

- MOSFETs, and other critical heat-contributing components. Modern notebook CPUs generally exhibit  $I_{LOAD} = I_{LOAD(MAX)} \times 80\%$ .
- 3) **Switching Frequency.** This choice determines the basic trade-off between size and efficiency. The optimal frequency is largely a function of maximum input voltage, due to MOSFET switching losses that are proportional to frequency and V<sub>IN</sub>2. The optimum frequency is also a moving target, due to rapid improvements in MOSFET technology that are making higher frequencies more practical.
- 4) Inductor Operating Point. This choice provides tradeoffs between size and efficiency. Low inductor values cause large ripple currents, resulting in the smallest size, but poor efficiency and high output noise. The minimum practical inductor value is one that causes the circuit to operate at the edge of critical conduction (where the inductor current just touches zero with every cycle at maximum load). Inductor values lower than this grant no further size-reduction benefit.
  - The MAX1718's pulse-skipping algorithm initiates skip mode at the critical conduction point. So, the inductor operating point also determines the load-current value at which PFM/PWM switchover occurs. The optimum point is usually found between 20% and 50% ripple current.
- 5) The inductor ripple current also impacts transient-response performance, especially at low V<sub>IN</sub> V<sub>OUT</sub> differentials. Low inductor values allow the inductor current to slew faster, replenishing charge removed from the output filter capacitors by a sudden load

step. The amount of output sag is also a function of the maximum duty factor, which can be calculated from the on-time and minimum off-time:

$$V_{SAG} = \frac{(I_{LOAD1} - I_{LOAD2})^2 \times L\left(K\frac{V_{OUT}}{V_{IN}} + t_{OFF(MIN)}\right)}{2 \times C_{OUT} \times V_{OUT}\left[K\left(\frac{V_{IN} - V_{OUT}}{V_{IN}}\right) - t_{OFF(MIN)}\right]}$$

where toff(MIN) is the minimum off-time (see the *Electrical Characteristics* tables) and K is from Table 2.

#### **Inductor Selection**

The switching frequency and operating point (% ripple or LIR) determine the inductor value as follows:

$$L = \frac{V_{OUT}(V_{IN} - V_{OUT})}{V_{IN} \times f_{SW} \times LIR \times I_{LOAD(MAX)}}$$

Example:  $I_{LOAD(MAX)} = 19A$ ,  $V_{IN} = 7V$ ,  $V_{OUT} = 1.25V$ ,  $f_{SW} = 300kHz$ , 30% ripple current or LIR = 0.30.

$$L = \frac{1.25V(7V - 1.25V)}{7V \times 300kHz \times 0.30 \times 19A} = 0.60\mu H$$

Find a low-loss inductor having the lowest possible DC resistance that fits in the allotted dimensions. Ferrite cores are often the best choice, although powdered iron is inexpensive and can work well at 200kHz. The core must be large enough not to saturate at the peak inductor current (IPEAK).

IPEAK = ILOAD(MAX) + (LIR / 2) ILOAD(MAX)

#### **Setting the Current Limit**

The minimum current-limit threshold must be great enough to support the maximum load current when the current limit is at the minimum tolerance value. The valley of the inductor current occurs at ILOAD(MAX) minus half of the ripple current; therefore:

where ILIMIT(LOW) equals the minimum current-limit threshold voltage divided by the RDS(ON) of Q2. For the MAX1718 Figure 1 circuit, the minimum current-limit threshold with VILIM = 105mV is about 95mV. Use the worst-case maximum value for RDS(ON) from the MOSFET Q2 data sheet, and add some margin for the rise in RDS(ON) with temperature. A good general rule is to allow 0.5% additional resistance for each °C of temperature rise.

Examining the Figure 1 example with a Q2 maximum RDS(ON) =  $3.8m\Omega$  at TJ =  $+25^{\circ}$ C and  $5.7m\Omega$  at TJ =  $+125^{\circ}$ C reveals the following:

$$I_{LIMIT(LOW)} = 95 \text{mV} / 5.7 \text{m}\Omega = 16.7 \text{A}$$

and the required valley current limit is:

$$I_{LIMIT(LOW)} > 19A - (0.30 / 2) 19A = 16.2A$$

Since 16.7A is greater than the required 16.2A, the circuit can deliver the full-rated 19A.

When delivering 19A of output current, the worst-case power dissipation of Q2 is 1.95W. With a thermal resistance of 60°C/W and each MOSFET dissipating 0.98W, the temperature rise of the MOSFETs is 60°C/W  $\times$  0.98W = 58°C, and the maximum ambient temperature is +125°C - 58°C = +67°C. To operate at a higher ambient temperature, choose lower RDS(ON) MOSFETs or reduce the thermal resistance. Raising the current-limit threshold allows for operation with a higher MOSFET junction temperature.

Connect ILIM to  $V_{CC}$  for a default 100mV current-limit threshold. For an adjustable threshold, connect a resistor divider from REF to GND, with ILIM connected to the center tap. The external adjustment range of 0.5V to 3.0V corresponds to a current-limit threshold of 50mV to 300mV. When adjusting the current limit, use 1% tolerance resistors and a 10 $\mu$ A divider current to prevent a significant increase of errors in the current-limit tolerance.

#### **Output Capacitor Selection**

The output filter capacitor must have low enough effective series resistance (ESR) to meet output ripple and load-transient requirements, yet have high enough ESR to satisfy stability requirements. Also, the capacitance value must be high enough to absorb the inductor energy going from a full-load to no-load condition without tripping the OVP circuit.

In CPU VCORE converters and other applications where the output is subject to violent load transients, the output capacitor's size typically depends on how much ESR is needed to prevent the output from dipping too low under a load transient. Ignoring the sag due to finite capacitance:

#### RESR ≤ VSTEP / ILOAD(MAX)

The actual microfarad capacitance value required often relates to the physical size needed to achieve low ESR, as well as to the chemistry of the capacitor technology. Thus, the capacitor is usually selected by ESR and volt-